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substrate is thus decreased to thereby form an opening forming region M, whereas a region of the substrate covered with the first coating is not etched to thereby form a thick portion [140]. Then, on a second surface of the substrate [(100)], a second coating is formed by applying a resist [(104)] at a region of the substrate other than where openings are to be formed in the region M. The substrate is then etched using the second coating as a mask to form holes, as openings [(101)], at regions not covered by the second coating. By using the thus obtained deposition mask [(100)] as a mask for evaporation, a material can be deposited to a desired location with high accuracy.

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IN THE CLAIMS:

N. ~~Claim 1, line 2, delete "including" and insert - -comprising:- -.~~

~~Claim 6, line 2, after "mask" insert - -is- -.~~

~~Claim 6, line 3, after "performed" insert - -and- -~~

~~Claim 9, line 2, delete "composed by arranging" and insert - -, said device including- -.~~